	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	D e f i	r
1	BRS	12 7	sonos with flash near memory	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/03 16:42			0
2	BRS	40	sonos with flash near memory and spacer	世野性ATPB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:29			0
3	BRS	19	sonos with flash near memory and spacer and tunnel\$ with nitride	1	2004/09/03 16:29			0
4	BRS		sonos with flash near memory and spacer and tunnel\$ with nitride and isolat\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:30			0
5	BRS	9	sonos with flash near memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:31			0
6	BRS	16	sonos with flash near memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 17:41			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e n	r D e f i	Errors
7	BRS	2	sonos with flash near memory and (two or double) with nitride with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:44			0
8	BRS	1	thones or sonos) with flash near memory and (two or double or dual or separats) with tunnels	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:45			0
9	BRS	4		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 17:41			0
10	BRS		flash near memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:48			0
11	BRS	31		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:39			0

	Тур	Hi ts	Search Text	DBs	Time Stam	q i	m m e	f	Errors
12	BRS	43	memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon		2004/09/0 18:38	4			0
13	BRS	42	(memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon) not (US-2004015743 4-A1.DID. and (flash near memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/0 18:39	4			0
14	BRS	31		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/0 18:39	4			0

	Тур	Hi	Search Text	DBs	Time Stamp	Comments	D e f	r
15	BRS	12	(memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon) not (flash near memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:39			0
16	BRS		memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon and ono with sacrificial and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:49			0
17	BRS			USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:50			0

	Тур е	Hi ts	Search Text	DBs	Time Stamp	m m e	f	E r o r
18	BRS		memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:52			0
19	BRS	67	TMEMOFY and spacer and tunnels with nitride and isolats and polysilicon and sacrificial) not (memory and (two or double or dual or separats or divids) with nitride with tunnels and spacer and polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 19:06			0
20	IS& R		("6596609").PN	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/04 19:08			0
21	IS& R	3	("6218224").PN	也多性 <u>A</u> 早身B US-PGPUB; EPO; JPO; DERWENT;	2004/09/04 19:09			0
	IS& R		("6103563").PN	也多样ATPB US-PGPUB; EPO; JPO; DERWENT;	2004/09/04 19:09			0
23	IS& R	2	: (''51)	世 島坪<u>A</u>早 身B US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/04 19:09			0